

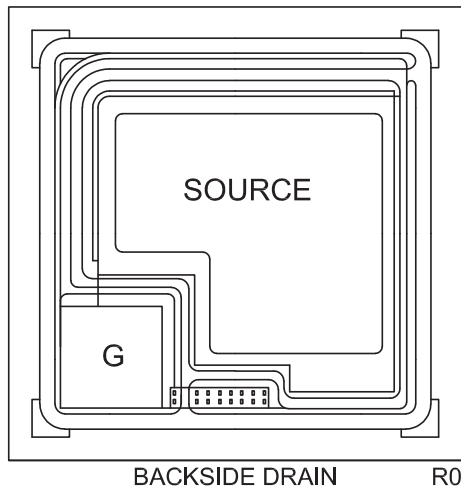
PROCESS CP328X
Small Signal MOSFET Transistor
N-Channel Enhancement-Mode MOSFET Chip



PROCESS DETAILS

Die Size	15.7 x 15.7 MILS
Die Thickness	5.5 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	9.1 x 8.1 MILS
Top Side Metalization	Al-Si 30,000Å
Back Side Metalization	Au - 9,000Å

GEOMETRY



GROSS DIE PER 6 INCH WAFER

95,200

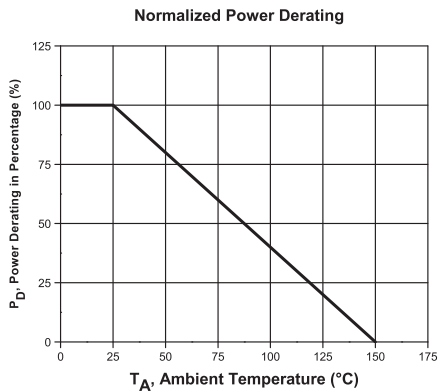
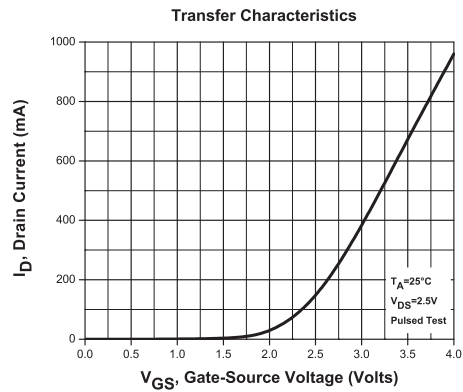
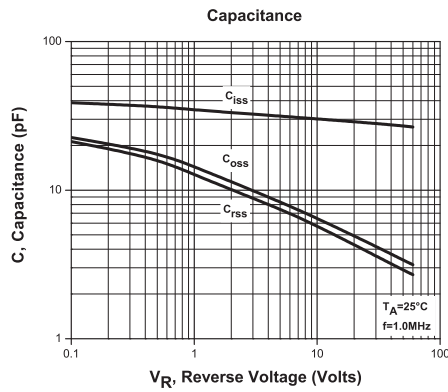
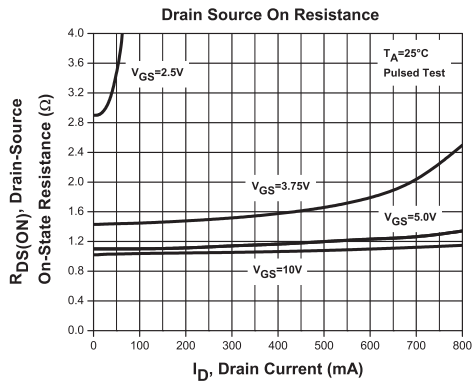
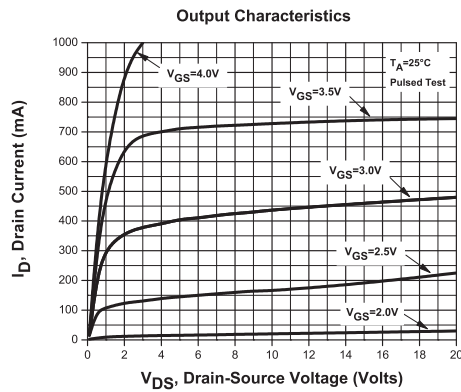
PRINCIPAL DEVICE TYPE

CMPDM7002AE

R0 (31-October 2012)

PROCESS CP328X

Typical Electrical Characteristics



R0 (31-October 2012)